

(List 2-3)

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>			
				Application Number		10/642,305	
				Filing Date		August 18, 2003	
				First Named Inventor		Hongyong ZHANG et al.	
				Art Unit		2811	
				Examiner Name		Douglas W. Owens	
Sheet	1	of	5	Attorney Docket Number		740756-2646	

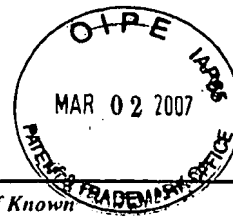
OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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/DWO/	1	PERRIN, J. et al., "Mass-Spectrometric Study of NF ₃ Plasma-Etching of Silicon", <u>Plasma Chemistry and Plasma Processing</u> , Vol. 10, No. 4, (1990) pp. 571-587	
/DWO/	2	GROVE, A.S., "Physics and Technology of Semiconductor Devices", Wiley (New York), (1967), p. 334.	
/DWO/	3	GORDON, R. "Chemical Vapor Deposition of Coatings on Glass", <u>Journal of Non-Crystalline Solids</u> , Vol. 218, (1997), pp. 81-91.	
/DWO/	4	BALK, P. et al. "Phosphosilicate Glass Stabilization of FET Devices", <u>Proceedings of the IEEE</u> , Vol. 57, No. 9, (September 1969), pp.1558-1563.	
/DWO/	5	PLUMMER et al.; "Silicon VLSI Technology: Fundamentals, Practice and Modeling"	
/DWO/	6	NICOLLIAN, E.H. et al.; "MOS (Metal Oxide Semiconductor Physics and Technology", Wiley (New York) p. 774.	
/DWO/	7	Sze S.M. (Author ADAMS, A.C.), "VLSI Technology" Wiley, (New York) (1983) pp. 93-129.	
/DWO/	8	KRIEGLER, R.J, "Neutralization of Na ⁺ Ions in HCl-Grown SiO ₂ ", <u>Applied Physics Letters</u> , Vol. 20, No. 11, (June 1, 1972), pp. 449-541.	
/DWO/	9	DEAL, B.E. et al. "Chlorine Concentration Profiles in 0.2-HCl and H ₂ O- HCl Thermal Silicon-Oxides Using Sims Measurements", <u>Journal of the Electrochemical Society</u> , Vol. 125, No. 12, (December 1978), pp. 2024-2027.	
/DWO/	10	ROHATGI, A. et al. "Sodium Passivation in HCl Oxide-Films on Si", <u>Applied Physics Letters</u> , Vol. 30, No. 2, (January 15, 1977) pp. 104-106.	

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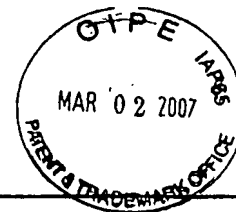
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/DWO/		ROHATGI A., et al. " <u>Chlorine Incorporation in HCl Oxides</u> ", <u>Journal of The Electrochemical Society</u> , Vol. 126, No. 1, (January 1979), pp. 143-148.	
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/DWO/		NISHIOKA, Y. et al. " <u>Dielectric Characteristics of Fluorinated Ultradry SiO₂</u> " <u>Applied Physics Letters</u> , Vol. 54, No. 12, (March 20, 1989), pp. 1127-1129	
/DWO/		NISHIOKA, Y. et al. " <u>Hot-Electron Hardened Si-Gate MOSFET Utilizing F-Implantation</u> ", <u>IEEE Electron Device Letters</u> , Vol. 10, No. 4, (April 1989), pp. 141-143.	
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/DWO/		JANSEN, F. et al. " <u>Contamination Effects in Glow-Discharge Deposition Systems</u> ", <u>Journal of Vacuum Science & Technology A</u> , Vol. 6, No. 1, (1988), pp. 13-18	
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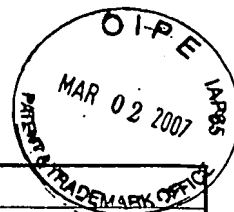
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/DWO/		KARULKAR, P.C. et al., "XPS AES Investigation of Cross Contamination in a Plasma Etcher", <u>Journal of Vacuum Science & Technology B</u> , Vol. 3, No. 3, (1985), pp. 889-891	
/DWO/		Exhibit 7, Asserted Claim Chart – Sano Reference, JP 64-35959	
/DWO/		FRANCOIS-SAINT-CYR, et al. "Diffusion of 18 elements implanted into thermally grown SiO ₂ ", <u>Journal of Applied Physics</u> , Vol. 94, No. 12, (December 15, 2003), pp. 7433-7439	
/DWO/		DATAR, S.A. et al. "AMS Studies of the Diffusion of Chlorine in Silicon-Wafers" <u>Nuclear Instruments & Methods in Physics Research- B 99</u> - Beam Interactions with Materials and Atoms, (1995), pp. 549-552	
/DWO/		TSENG, H.H. et al. "Fluorine Diffusion on a Polysilicon Grain-Boundary Network in Relation to Boron Penetration from P+ Gates", <u>IEEE Electron Device Letters</u> , Vol. 13, No. 1, (January 1992), pp. 14-16	
/DWO/		TROXELL, JOHN R. et al. "Polycrystalline Silicon Thin-Film Transistors on a Novel 800°C Glass Substrate", <u>IEEE Electron Device Letters</u> , Vol. 7, No. 11, (November 1986), pp. 597-599	
/DWO/		ERMOLIEFF, A. et al. "XPS Studies of Contamination of Reactor and Silicon Surfaces Caused by Reactive Ion Etching", <u>Semiconductor Science and Technology</u> , Vol. 6, (1991), pp. 290-295	
/DWO/		ERMOLIEFF, A. et al. "X-Ray Photoelectron-Spectroscopy Studies of Contamination and Cleaning of Surfaces Exposed to a Fluorocarbon Plasma", <u>Journal of Vacuum Science & Technology A</u> , Vol. 9, No. 6, (November/December 1991), pp. 2900-2906	

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/DWO/		HUGHES, C. et al. "In-situ HDP-CVD Process Diagnostics Based on Quadrupole Mass Spectrometry", (IMEC Leuven, Belgium)	
/DWO/		IQBAL, Z. et al. "Raman scattering from hydrogenated microcrystalline and amorphous silicon", <u>J. Phys. C. Solid State Phys.</u> , Vol. 15 (1982) pp. 377-392	
/DWO/		JENG, S.P. et al. "Anomalous Diffusion of Fluorine in Silicon", <u>Applied Physics Letters</u> , Vol. 61, No. 11, (September 14, 1992), pp. 1310-1312	
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/DWO/		PINARBASI, M. et al., "Hydrogenated Amorphous Silicon Films Deposited by DC Planar Magnetron Reactive Sputtering", <u>Superlattices and Microstructure</u> , Vol. 3, No. 4, (1987) pp. 331-340	
/DWO/		MADAN, A. et al. "Characterization of Schottky Barriers", <u>The Physics and Applications of Amorphous Semiconductors</u> , Academic Press, pp. 193-197	
/DWO/		MADAN et al. "Use of PECVD System in Thin Film Technology", Workshop on Industrial Plasma Applications, pp. 1-10	
/DWO/		MALEY, N. et al. "Infrared absorption and thermal evolution study and hydrogen bonding in a-SiH", <u>Journal of Vacuum Science & Technology</u> , Vol. 7, No. 3, (May/June 1989), pp. 1267-1270	

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		Number - Kind Code ² (if known)			
/DWO/		US-4,007,294	02/08/1977	Woods et al.	
/DWO/		US-4,485,146	11/27/1984	Mizuhashi et al..	
/DWO/		US-4,657,616	04/14/1987	Benzing et al.	
/DWO/		US-4,786,352	11/22/1988	Benzing	
/DWO/		US-4,851,363	07/25/1989	Troxell et al.	
/DWO/		US-7,097,716 B2	08/29/2006	Barnes et al.	
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FOREIGN PATENT DOCUMENTS

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/DWO/		JP	64-35959	02/07/1989			
/DWO/		JP	01-268064	10/25/1989			FULL

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/DWO/	1	Toppoly's Opposition Claim Construction Brief, May 30, 2006	
/DWO/	2	Declaration of Hector G. Gallegos in Support of Toppoly Optoelectronics Corp.'s Opposition Claim Construction Brief, May 30, 2006	
/DWO/	3	Plaintiff and Counterclaim Defendant Semiconductor Energy Laboratory Co., Ltd.'s Memorandum of Points and Authorities in Opposition to Defendants' and Counterclaim Plaintiffs' Claim Construction Brief (signed on 05/26/2006), May 30, 2006	
/DWO/	4	Supplemental Declaration of Reginald J. Hill in Support of Semiconductor Energy Laboratory Co., Ltd.'s Claim Constructions (signed on 05/26/2006); May 30, 2006	
/DWO/	5	Toppoly Optoelectronics Corp.'s Supplemental Response to Semiconductor Energy Laboratory Co., Ltd.'s Interrogatory No. 4, June 21, 2006	
/DWO/	6	Order: Claim Construction Ruling, July 25, 2006	
/DWO/	7	Invalidity Report of Professor Gottlieb S. Oehrlein, September 22, 2006	
/DWO/	8	Expert on the Invalidity of U.S. Patents 5,352,291, Zhang et al. No. 6,177,302B1, Yamazaki et al., and No. 6,566,175B2, Yamazaki et al., by S. Wagner, September 24, 2006	

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